

# Contents

<b>1</b>	<b>A Brief Introduction to the Topic .....</b>	1
1.1	Mesoscopic Semiconductor Structures .....	1
1.2	Self-Organized Fabrication .....	2
1.3	X-Ray Diffuse Scattering .....	2
1.4	How Is this Book Organized? .....	4
	References .....	5
<b>2</b>	<b>Basic Principles of X-Ray Diffuse Scattering from Mesoscopic Structures .....</b>	7
2.1	Choice of Appropriate Scattering Theory .....	7
2.2	Interaction of Hard X-Rays with Matter .....	9
2.2.1	The Dielectric Polarizability .....	9
2.2.2	Reflection, Refraction, and Absorption of X-Rays .....	10
2.2.3	Effect of Roughness on Reflectivity and Transmittivity .....	16
2.3	Kinematical Scattering Theory .....	17
2.3.1	The Born Approximation .....	17
2.3.2	Strain-Induced Diffuse Scattering .....	20
2.3.3	Numerical X-Ray Simulations Using the Finite-Element Method .....	25
2.3.4	Influence of Positional Correlation .....	28
2.3.5	Small-Angle X-Ray Scattering .....	36
2.4	Dynamical Scattering Theory .....	38
2.5	The Distorted-Wave Born Approximation .....	41
2.5.1	Single-Channel DWBA .....	44
2.5.2	GISAXS from Free-Standing Islands: 5-Channel DWBA .....	46
2.5.3	Grazing-Incidence Diffraction from Free-Standing Islands: 9- and 16-Channel DWBA .....	48
2.6	Scattering from Surface and Interface Roughness .....	50
2.6.1	Scattering Cross Section .....	52
2.6.2	Statistical Description of Roughness: the Self-Affine Model .....	54
2.6.3	Vertical Inheritance of Interface Roughness in Multilayers .....	56

## VIII Contents

2.6.4	Statistical Description of Roughness: the Step Model..	60
2.6.5	Effect of Roughness on Grazing-Incidence Diffraction .	61
References .....		62
<b>3</b>	<b>Experimental Optimization .....</b>	69
3.1	Requirements .....	69
3.2	Synchrotron Radiation .....	70
3.2.1	Beam Collimation .....	70
3.2.2	Energy Resolution .....	71
3.3	Coherence of X-Rays.....	72
3.3.1	Coherence Lengths .....	72
3.3.2	Grazing-Incidence Conditions .....	73
3.3.3	Influence of a Position-Sensitive Detector on the Measured Coherence Lengths .....	74
3.3.4	Influence of Limited Coherence on the X-Ray Diffraction Pattern .....	74
3.4	Scattering Geometries: the Extended Ewald Sphere .....	75
3.5	Multidetection Techniques .....	77
3.5.1	Basic Principle .....	77
3.5.2	Area Detectors .....	78
3.6	Scattering Techniques .....	81
3.6.1	Coplanar High-Resolution Diffraction .....	81
3.6.2	Grazing-Incidence Diffraction .....	83
3.6.3	Grazing-Incidence Small-Angle X-Ray Scattering .....	85
3.7	Experimental Resolution .....	89
3.8	Scans in Reciprocal Space .....	90
3.9	Critical Comparison of Scattering Techniques .....	91
References .....		93
<b>4</b>	<b>A Model System: LPE SiGe/Si(001) Islands .....</b>	95
4.1	A Brief Introduction to Stranski-Krastanow Growth .....	95
4.2	LPE Growth of SiGe Islands .....	97
4.3	Shape Evolution.....	99
4.4	Determination of Shape and Size by GISAXS .....	102
4.5	Strain Field and Chemical Composition Profile .....	105
4.6	Geometrical Aspect Ratio .....	111
4.7	Island–Island Correlation .....	114
4.7.1	Evolution of Island Rows .....	114
4.7.2	Quantitative Analysis of Island Ordering .....	117
4.7.3	The Autocorrelation Function in Real Space .....	120
4.7.4	Inclusion of Spatial Correlation in X-Ray Simulations .	121
References .....		124

<b>5</b>	<b>Dynamical Scattering Effects at Grazing Incidence Conditions</b>	127
5.1	Grazing-Incidence Small-Angle X-Ray Scattering	127
5.2	Grazing-Incidence Diffraction	131
	References	137
<b>6</b>	<b>Characterization of Quantum Dots</b>	139
6.1	Structural Properties of Quantum Dots	139
6.2	Free-Standing InP Quantum Dots	141
6.2.1	Surface Morphology	141
6.2.2	Experimental Results	143
6.2.3	Simulation of X-Ray Diffuse Scattering	145
6.2.4	Strain Relaxation Versus Geometrical Aspect Ratios	147
6.2.5	Size and Shape Homogeneity	149
6.3	Buried InP Quantum Dots	150
6.3.1	Polarization Anisotropy of Photoluminescence	150
6.3.2	Shape and Strain Relaxation	152
6.3.3	Lateral and Vertical Correlation	155
6.4	Buried InGaAs Quantum Dots	156
6.4.1	Shape Analysis	156
6.4.2	Chemical Composition	160
6.4.3	Lateral Correlation	161
	References	161
<b>7</b>	<b>Characterization of Interface Roughness</b>	165
7.1	Roughness in Vicinal Semiconductors	165
7.2	Effect of Atomic Steps on the Diffuse Scattering of X-Rays	166
7.3	Anisotropic Interfacial Roughness	167
7.4	Vertical Inheritance of Interface Roughness	170
7.4.1	Inclined Inheritance	170
7.4.2	Determination of Inclination Angles by a Simple Model	172
7.4.3	Limits of Applicability of Ellipsoidal Model	174
7.5	Effect of Roughness in Grazing-Incidence Diffraction	176
7.6	Ordered Linear Structures	179
	References	184
<b>A</b>	<b>Appendix</b>	187
A.1	The Resolution Function in Reciprocal Space	187
A.1.1	General Expression	187
A.1.2	High-Resolution X-Ray Diffraction	187
A.1.3	Grazing-Incidence Diffraction	188
A.1.4	Grazing-Incidence Small-Angle X-Ray Scattering	189

A.2	Strain Analysis by the Finite-Element Method . . . . .	189
A.2.1	A Very Brief Survey of Linear Elasticity Theory . . . . .	189
A.2.2	Equilibrium Conditions . . . . .	192
A.2.3	The Finite-Element Method . . . . .	192
A.2.4	FEM as Input for X-Ray Scattering Simulations . . . . .	193
A.3	List of Acronyms . . . . .	194
A.4	List of Symbols . . . . .	195
A.5	Physical Constants . . . . .	197
	References . . . . .	197
<b>Index</b>	.....	199